

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	540	semiconductor and MOS and (body) and source and (band adj gap) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 06:24
L2	2	(semiconductor with MOS with (body) with source with (band adj gap)) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 06:25
L3	6	(semiconductor same MOS same (body) same source same (band adj gap)) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 06:25
L4	41	438/197,270,271.ccls. and (band adj gap) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 07:30
S1	8	((("6172398") or ("6133107") or ("5698867") or ("5821144")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/09 12:25
S2	0	438/197,270,271.ccls. and (tile adj angle) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/09 12:44
S3	4	438/197,270,271.ccls. and (tilt adj (implant\$6 or dop\$6)) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/09 12:45
S4	15666	semiconductor and (band adj gap) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 06:24
S5	10538	(semiconductor same (band adj gap)) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 10:51

S6	8320	(semiconductor with (band adj gap)) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 10:51
S7	1002	((semiconductor with (band adj gap)) and @ad<="20011012") and ((metal adj oxide adj semiconductor) or ("MOS"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 11:53
S8	872	((semiconductor with (band adj gap)) and @ad<="20011012") and ((metal adj oxide adj semiconductor) or ("MOS")) and source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 11:53
S9	680	((semiconductor with (band adj gap)) and @ad<="20011012") and ((metal adj oxide adj semiconductor) or ("MOS")) and source and within	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 11:54
S10	265	((semiconductor with (band adj gap)) and @ad<="20011012") and ((metal adj oxide adj semiconductor) or ("MOS")) and (source same within)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 11:54
S11	151	((semiconductor with (band adj gap)) and @ad<="20011012") and ((metal adj oxide adj semiconductor) or ("MOS")) and (source with within)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:14
S12	843	(438/197).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/03 12:12
S13	1706	(438/270).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/03 12:12
S14	359	(438/271).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/03 12:13

S15	1106	(257/288).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/03 12:13
S16	694	(257/335).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/03 12:13
S17	40	438/197,270,271.ccls. and (band adj gap) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 07:30
S18	58	257/288,335,336,337,338,339,340,341,342,343.ccls. and (band adj gap) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:14
S19	6498	"257"/\$.ccls. and (band adj gap) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:15
S20	2479	"438"/\$.ccls. and (band adj gap) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:15
S21	1066	"257"/\$.ccls. and (band adj gap) and ((metal adj oxide adj semiconductor) or ("MOS")) and source and within and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:15
S22	425	"438"/\$.ccls. and (band adj gap) and ((metal adj oxide adj semiconductor) or ("MOS")) and source and within and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:16
S23	198	"438"/\$.ccls. and (band adj gap) and ((metal adj oxide adj semiconductor) or ("MOS")) and (source same within) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:16
S24	487	"257"/\$.ccls. and (band adj gap) and ((metal adj oxide adj semiconductor) or ("MOS")) and (source same within) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:16

S25	128	"438"/\$.ccls. and (band adj gap) and ((metal adj oxide adj semiconductor) or ("MOS")) and (source with within) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:17
S26	300	"257"/\$.ccls. and (band adj gap) and ((metal adj oxide adj semiconductor) or ("MOS")) and (source with within) and @ad<="20011012"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/06 11:29
S27	2	("6765247").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/09 12:24
S28	13	("4564770" "4969852" "5138177" "5698867" "5821144" "6035235" "6133107" "6143042" "6166520" "6166925" "6172398" "6239958" "6368920" "2001/0048119" "2002/0017684").PN.	USPAT	OR	ON	2004/08/06 12:40
S29	8	((("5698867") or ("6133107") or ("6172398") or ("5821144"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/09 06:37
S30	6168	((standard adj litter adj per adj minute) or ("SLM"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:27
S31	792	((standard adj litter adj per adj minute) or ("SLM")) and (polysilicon or (poly adj ("Si")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:28
S32	214	((standard adj litter adj per adj minute) or ("SLM")) and (polysilicon or (poly adj ("Si")) and grain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:29
S33	201	((standard adj litter adj per adj minute) or ("SLM")) and (polysilicon or (poly adj ("Si")) and grain and @ad<="20030507"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:30

S34	4	((standard adj litter adj per adj minute) or ("SLM")) same (polysilicon or (poly adj ("Si"))) same grain) and @ad<="20030507"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:32
S35	2	((standard adj litter adj per adj minute) or ("SLM")) with (polysilicon or (poly adj ("Si"))) with grain) and @ad<="20030507"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:31
S36	4	((standard adj litter adj per adj minute) or ("SLM")) same (polysilicon or (poly adj ("Si"))) same grain) and nitrogen and @ad<="20030507"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:32
S37	2	((standard adj litter adj per adj minute) or ("SLM")) with (polysilicon or (poly adj ("Si"))) with grain) and nitrogen and @ad<="20030507"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/03 12:32
S38	2	("6734478").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/09 06:41
S39	1	("20040132285").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/09 06:48
S40	2	("6,178,034").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/09 06:48